

Small Signal Switching Diodes



CDSH3- 222N/-G/222P-G

Reverse Voltage: 80 Volts
Pd: 150mW
RoHS Device



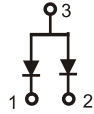
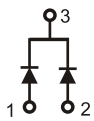
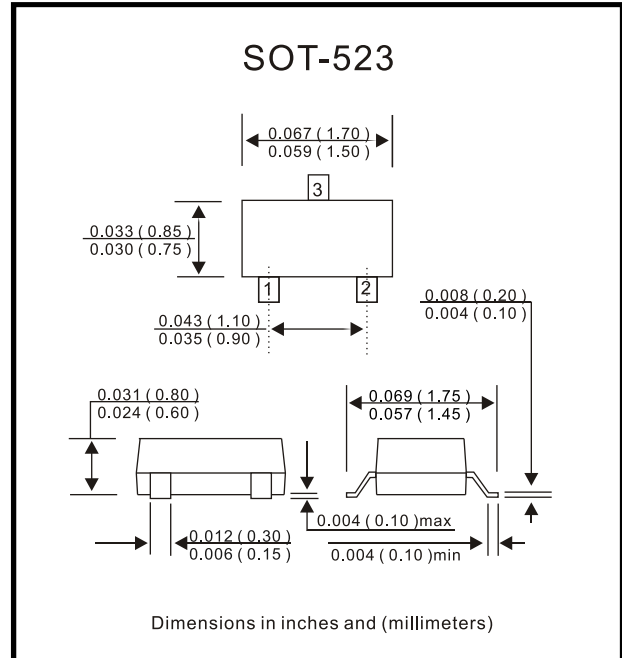
Features

- Designed for mounting on small surface.
- High speed switching.
- High mounting capability, strong surge withstand, high reliability.

Mechanical data

- Case: SOT-523, molded plastic.
- Terminals: Solder plated, solderable per MIL-STD-750, method 208.
- Approx. weight: 0.002 gram

CDSH3-222N-G CDSV3-222P-G



Maximum Ratings and Electrical Characteristics (at Ta = 25°C unless otherwise noted)

Parameter	Condition	Symbol	Value	Unit
Repetitive peak reverse voltage		V _{RRM}	80	V
Reverse voltage		V _R	80	V
Forward continue current		I _{FM}	300	mA
Surge peak forward current	T = 1.0 uS	I _{FSM}	4	A
Power dissipation		P _d	150	mW
Maximum forward voltage	@ I _F = 100 mA	V _F	1.2	V
Maximum reverse current	@ V _R = 70V	I _R	0.1	uA
Max reverse recovery time	I _F =I _R =5mA, R=100 ohms	T _{rr}	4	nS
Maximum diode capacitance	V _R =6V, f=1MHz	C _T	3.5	pF
Max. operation junction temperature		T _j	150	°C
Storage temperature		T _{STG}	-55 to +150	°C

RATING AND CHARACTERISTIC CURVES (CDSH3-222N-G/222P-G)

Fig. 1 - Forward characteristics(P Type)

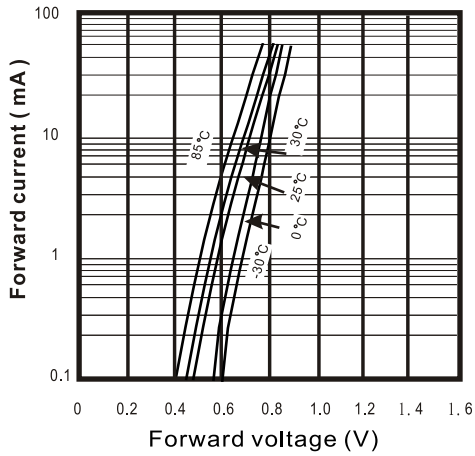


Fig. 2 - Reverse characteristics(P Type)

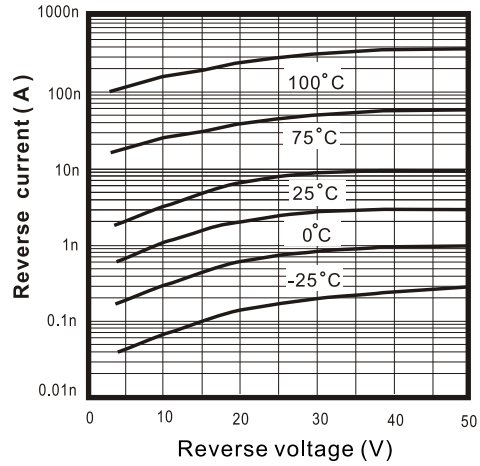


Fig. 3 - Forward characteristics(N Type)

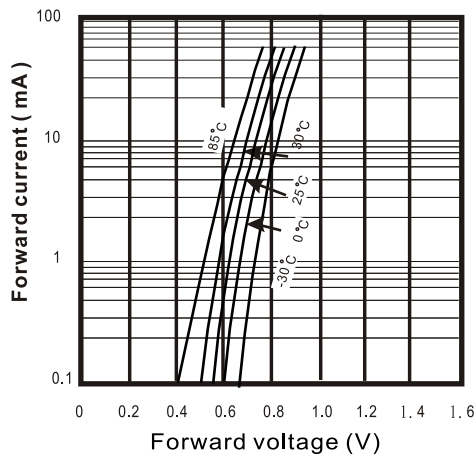


Fig. 4 - Reverse characteristics(N Type)

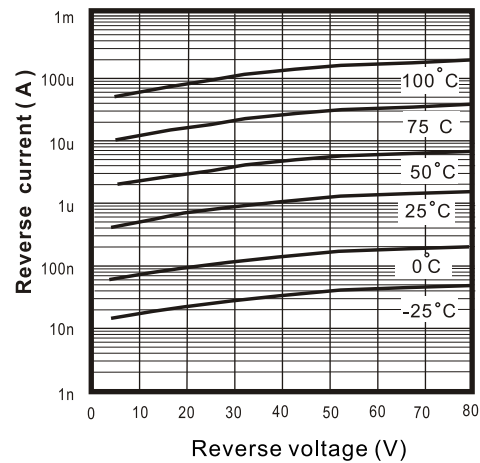


Fig. 5 - Capacitance between terminals characteristics

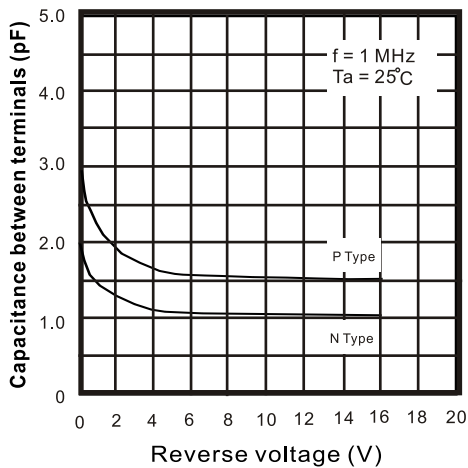


Fig. 6 - Power attenuation curve

